

<b>INFORMATION DISCLOSURE STATEMENT</b>	Atty Docket:	62601
	Serial No.:	10/647,060
	Applicant:	MEARS
	Filing Date:	AUGUST 22, 2003
	Group:	


U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
TTN	AA	4,594,603	06/10/86	Holonyak, Jr.	357	16	01/24/85
I	AB	4,937,204	06/26/90	Ishibashi et al.	437	110	01/4/89
TTN	AC	4,969,031	11/06/90	Kobayashi et al.	357	63	02/3/83
	AD	5,05,887	10/08/91	Yamazaki	357	4	01/18/90
TTN	AE	5,216,262	06/1/93	Tsu	257	17	03/2/92
	AF	5,357,119	10/18/94	Wang et al.	257	18	02/19/93
	AG	5,684,817	11/04/97	Houdre et al.	372	45	05/1/96
	AH	5,683,934	11/4/03	Candelaria	437	134	05/3/96
	AI	5,994,164	11/30/99	Fonash et al.	438	97	03/18/98
	AJ	6,058,127	05/2/00	Joannopoulos et al.	372	92	12/12/97
	AK	6,274,007	08/14/01	Smimov et al.	204	192	03/14/00
	AL	6,281,518	08/28/01	Sato	257	13	12/3/98
	AM	6,281,532	08/28/01	Doyle et al.	257	288	06/28/99
	AN	6,344,271	02/05/02	Yadav et al.	428	402	03/23/99
	AO	6,472,685	10/29/02	Takagi	257	77	12/2/98
	AP	6,498,359	12/24/02	Schmidt et al.	257	190	05/18/01
	AQ	2003/ 0034529	02/20/03	Fitzgerald et al.	257	369	10/8/02
TTN	AR	2003/ 0057416	03/27/03	Currie et al.	257	19	09/20/02
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation
TTN	AS	02/103767	12/27/02	WO	H01L	21/20	
TTN	AT	2,347,520	09/06/00	GB	G02B	5/18	
	AU						

<b>EXAMINER:</b> 	<b>DATE CONSIDERED:</b> 11/18/04
<b>*EXAMINER:</b> Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

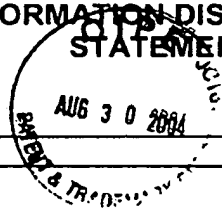


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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
TTN	AV	Xuan Luo et al.; "Chemical Design of Direct-Gap Light-Emitting Silicon", published July 25, 2002 by The American Physical Society; Vol. 89, Number 7
TTN	AW	R. Tsu; University of North Carolina at Charlotte, "Phenomena in Silicon Nanostructure Devices"; published 09/06/2000 © Springer-Verlag 2000
TTN	AX	P.D. Ye et al., "GaAs MOSFET with Oxide Gate Dielectric Grown by Atomic Layer Deposition"; © 2003 Agere Systems, March 2003
TTN	AY	Novikov et al.; "Silicon-based Optoelectronics" © 1999-2003 by John Wiley & Sons, Inc.; pp/ 1-6
	AZ	
	BA	


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U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
TTN	AA	4,485,128	11/27/84	Dalal et al.	427	85	
	AB	6,326,311	12/4/01	Ueda et al.	438	694	
	AC	6,350,993	2/26/02	Chu et al.	257	19	
	AD	6,376,337	4/23/02	Wang et al.	438	478	
	AE	6,436,784	8/20/02	Allam	438	380	
	AF	6,501,092	12/31/02	Nikonov et al.	257	29	
	AG	6,566,679	5/20/03	Nikonov et al.	257	29	
	AH	6,621,097	9/16/03	Nikonov et al.	257	17	
	AI	2003/0162335	8/28/03	Yuki et al.	438	151	3/4/03
TTN	AJ	2003/0215990	11/20/03	Fitzgerald et al.	438	172	3/14/03
	AK						
	AL						
	AM						
	AN						
	AO						

FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation
TTN	AP	61220339A	9/30/86	Japan	H01L21	322	English Abstract
TTN	AQ	61145820A	7/3/86	Japan	H01L21	20	English Abstract
TTN	AR	99/63580	12/9/99	WO	H01L3	00	n/a

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